

Silicon PNP Power Transistors

BD534/536/538

DESCRIPTION

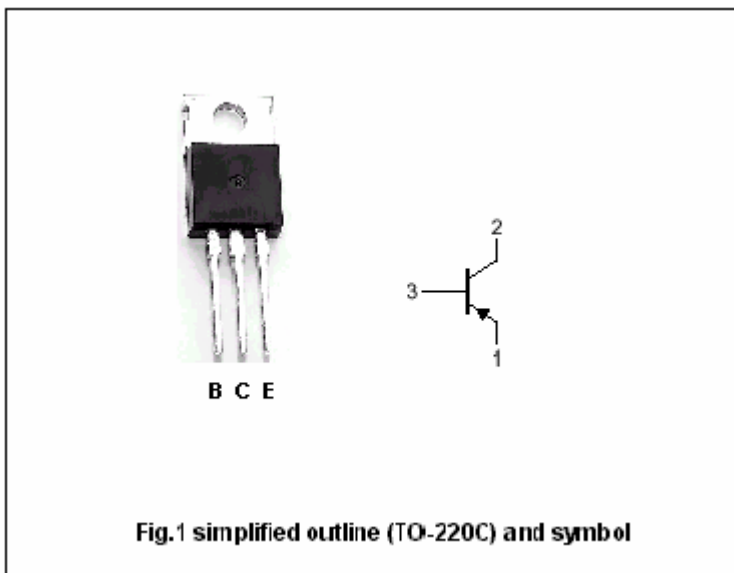
- With TO-220C package
- Complement to type BD533/535/537
- Low saturation voltage

APPLICATIONS

- For medium power linear and switching applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	BD534	-45	V
		BD536	-60	
		BD538	-80	
V _{CEO}	Collector-emitter voltage	BD534	-45	V
		BD536	-60	
		BD538	-80	
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-8	A
I _E	Emitter current		-8	A
I _B	Base current		-1	A
P _C	Collector power dissipation	T _C =25	50	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-65~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEsat-1}	Collector-emitter saturation voltage		I _C =-2 A; I _B =-0.2 A			-0.8	V
V _{CEsat-2}	Collector-emitter saturation voltage		I _C =-6 A; I _B =-0.6 A		-0.8		V
V _{BE}	Base-emitter on voltage		I _C =-2A ; V _{CE} =-2V			-1.5	V
I _{CBO}	Collector cut-off current	BD534	V _{CB} =-45V; I _E =0			-0.1	mA
		BD536	V _{CB} =-60V; I _E =0				
		BD538	V _{CB} =-80V; I _E =0				
I _{CES}	Collector cut-off current	BD534	V _{CE} =-45V; V _{BE} =0			-0.1	mA
		BD536	V _{CE} =-60V; V _{BE} =0				
		BD538	V _{CE} =-80V; V _{BE} =0				
I _{EBO}	Emitter cut-off current		V _{EB} =5V; I _C =0			-1	mA
h _{FE-1}	DC current gain	BD534/536	I _C =-10mA ; V _{CE} =-5V	20			
		BD538		15			
h _{FE-2}	DC current gain		I _C =-0.5A ; V _{CE} =-2V	40			
h _{FE-3}	DC current gain (All device)	Group: J	I _C =-2A ; V _{CE} =-2V	30		75	
		Group: K		40		100	
h _{FE-4}	DC current gain (All device)	Group: J	I _C =-3A ; V _{CE} =-2V	15			
		Group: K		20			
f _T	Transition frequency		I _C =-0.5A ; V _{CE} =-1V	3	12		MHz

PACKAGE OUTLINE

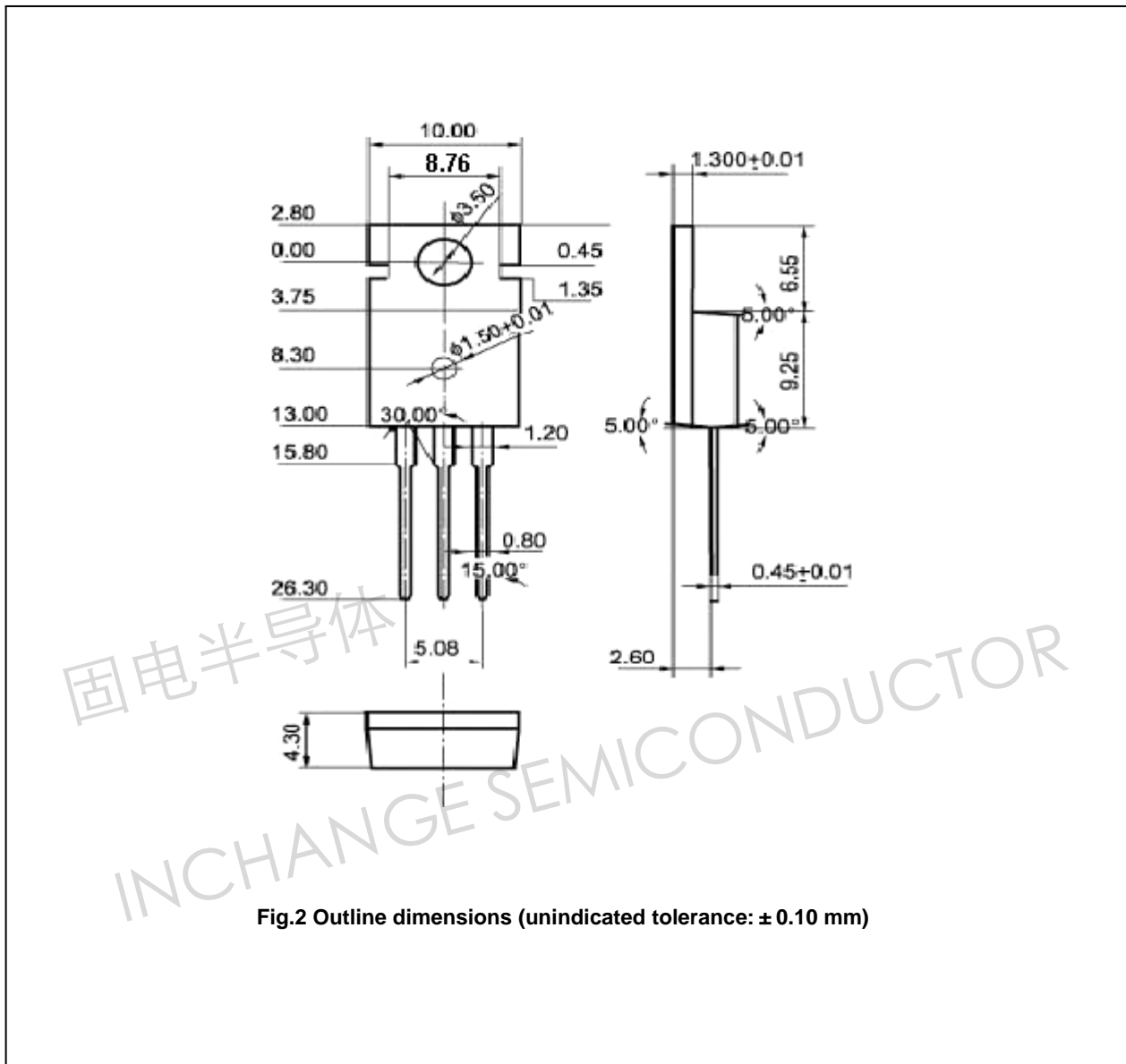


Fig.2 Outline dimensions (unindicated tolerance: ± 0.10 mm)